a semiconductor substrate;

at least two semiconductor components provided on the principal surface of the substrate;

electrodes of the at least two components provided on the substrate so as to substantially eliminate the electrical interference between the two semiconductor components;

a first group of through holes, which pass from the principal surface through the backside of the substrate and are provided in respective regions of the substrate under the electrodes;

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a first conductor film provided on the side faces of the first group of through holes;

a second group of through holes, which differ from the first group of through holes, which pass from the principal surface through the backside of the substrate between the components;

a second conductor film provided on the side faces of the second group of through holes; and

a wiring layer, which is provided on the backside of the substrate and is in contact with the first and second conductor films.

Please add new claims 8, 9 and 10 as follows:

-- 8. The device of Claim 1, where in the multiple through holes stand in a line.

9. A semiconductor device comprising:

a semiconductor substrate;

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at least two semiconductor components provided on the principal surface of the substrate;

multiple through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate between at least the two components so as to substantially eliminate the electrical interference between at least the two semiconductor components; and

a conductor film formed on the side faces of the through holes.